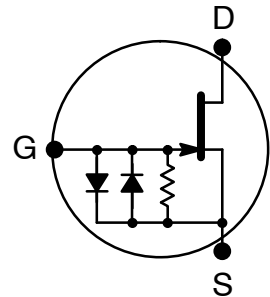




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**NTE2917
 MOSFET
 Silicon N-Channel JFET Transistor
 w/Internal Diode for ECM Impedance
 Converter Applications
 TO92S Type Package**



Features:

- Compact Package
- High Forward Transfer Admittance
- Low Capacitance
- Includes Diode and High Resistance at G – S

Absolute Maximum Ratings:

Drain-to-Source Voltage ($V_{GS} = -1.0V$), V_{DSX}	20V
Gate-to-Drain Voltage, V_{GDO}	-20V
Drain Current, I_D	10mA
Gate Current, I_G	10mA
Total Power Dissipation, P_T	100mW
Operating Junction Temperature, T_J	+125°C
Storage Temperature Range, T_{stg}	-55° to +125°C

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Zero Gate Voltage Drain Cutoff Current	I_{DSS}	$V_{DS} = 5V, V_{GS} = 0V$	60	-	500	μA
Gate Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = 5V, I_D = 1.0\mu A$	-	-	-1.0	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 5V, I_D = 30\mu A, f = 1kHz$	150	-	-	μs
		$V_{DS} = 5V, V_{GS} = 0V, f = 1kHz$	150	1200	-	μs
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 5V, f = 1MHz$	-	4.5	6.0	pF
Output Capacitance	C_{oss}		-	1.5	3.0	pF
Reverse Transfer Capacitance	C_{rss}		-	1.2	3.0	pF
Noise Voltage	NV		-	1.0	3.0	μV

